

# A System for measuring Temperature dependent Surface Photovoltage

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# Outline

Introduction

Theory

The Systems

Experimental

Discussion & Conclusion



# Motivation

## The goal of this project is to...

- Use a new experimental Kelvin Probe (KP) system
- Add illumination to 'new' KP
- Compare results from 'new' KP to established, 'old' KPs
  - Does 'old' & 'new' Contact Potential Difference (CPD) agree?
  - Does 'old' & 'new' Surface Photovoltage (SPV) agree?
- Ultimately measure temperature dependent Surface Photovoltage (SPV(T)) with the new system

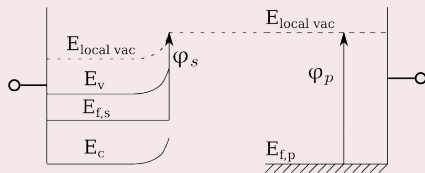
# The Contact Potential Difference (CPD)

## Physical Causes of CPD

The CPD is the difference in local vacuum levels, here defined as:

$CPD \equiv \varphi_{\text{Probe}} - \varphi_{\text{Sample}}$ ,  
where  $\varphi$  is Work function

### Semiconductor-Metal:



[1]

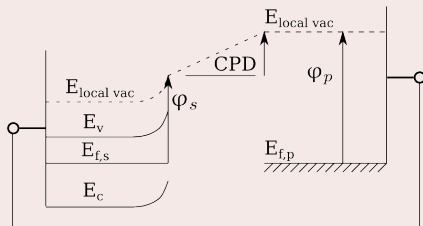
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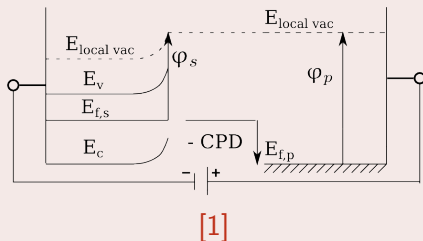
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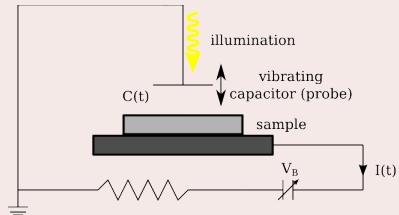


# The Contact Potential Difference (CPD)

## Measuring CPD: The Kelvin Probe (KP)

$$I(t) = \frac{dQ}{dt} = (CPD + V_b) \frac{dC}{dt}$$

$$I(t) = 0 \quad \text{iff} \quad V_b = -CPD$$



# Physical Causes of Surface Photovoltage (SPV)

## SPV: CPD in the dark dark vs. light

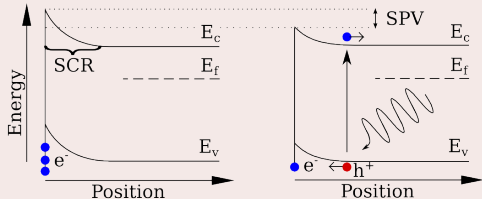
Different surface potentials in light and dark yield SPV:

$$\text{SPV} \equiv \text{CPD}_l - \text{CPD}_d$$

$$\equiv \varphi_{s,d} - \varphi_{s,l}$$

$$\text{SPV}_n > 0$$

$$\text{SPV}_p < 0$$

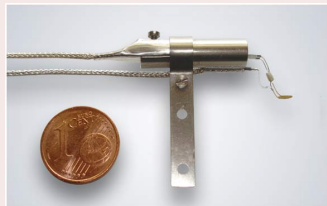




# Established, 'old' KP Systems

## Ambient & Glovebox KPs

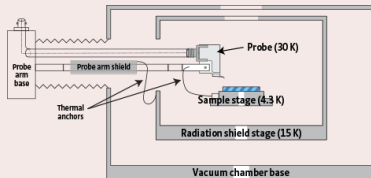
- Besocke KP head & controller
- Humidity controlled ambient
- Glovebox ( $< 5\text{ppm O}_2$  &  $\text{H}_2\text{O}$ )
- Xenon lamp & VariAC ( $\sim 80\text{ W}$ )
- Illumination is source of heat!



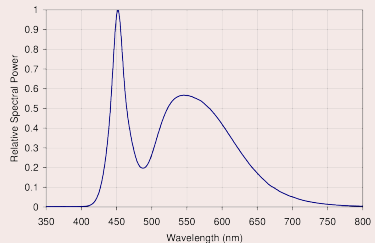
[2]

## 'New' System: Cryostat with a KP

### Lakeshore Cryostat with Mc Allister KP & LED illumination



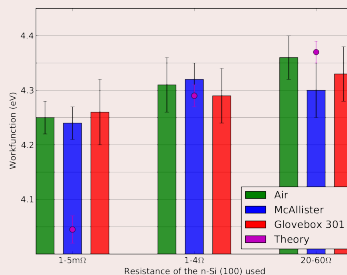
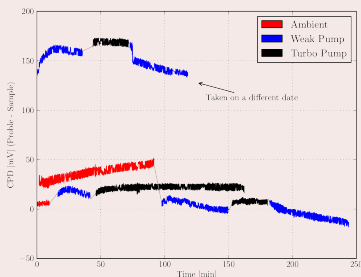
[3]



[4]

# Checking against Established Systems

## Behaviour at Room Temperature



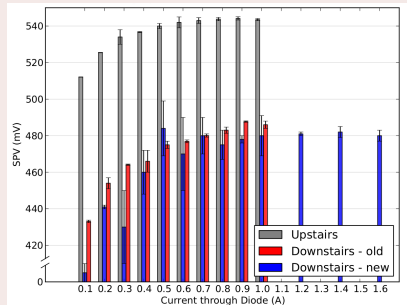
'Jumps' probably due to movement of probe head  
Excellent agreement between systems

# Checking against Established Systems

## Behaviour at lower temperatures and SPV

30 nm  $\text{AlO}_3$  on Si,  
by plasma-enhanced  
atomic layer deposition [5]

- $\Phi_{\text{Si/Alumina}}$  at 300 K:  
( $4.42 \pm 0.03$ ) eV
- $\Phi_{\text{Si/Alumina}}$  at 250 K:  
( $4.44 \pm 0.04$ ) eV

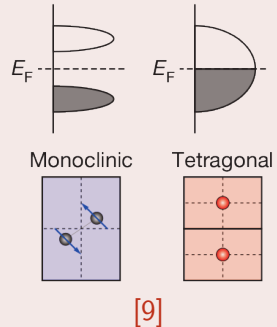


Probably no ice, even on very hydrophilic surface  
SPV  $\sim 12\%$  too low compared to other system and literature ([5]).  
Shadows on the sample?

# Intermission: Choosing a Model System for SPV(T)

## Metal Insulator (MI) Transition in $\text{VO}_2$

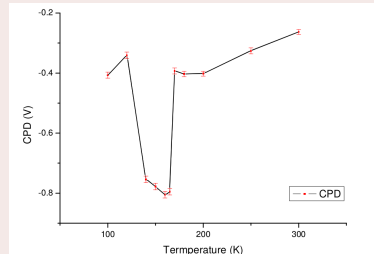
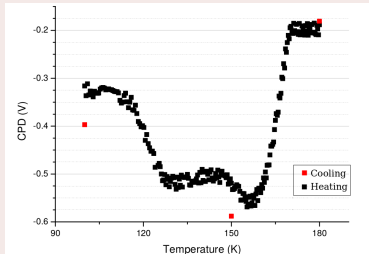
- metal at  $T > T_{MI}$
- semiconductor at  $T < T_{MI}$
- insulator at  $T \ll T_{MI}$
- $T_{MI} \approx 270 \text{ K}$  [6] (W-doped)
- $\phi \approx 5.15 \text{ eV}$  [7] (at RT)
- $\Delta\phi_{MI} \approx -0.15 \text{ eV}$  [7]
- $\Delta\phi_{MI} \approx 0.45 \text{ eV}$  [8] (W-doped)



# Temperature Dependent CPD in W:VO<sub>2</sub>

## Two independent Measurements: Sweep and Stabilise

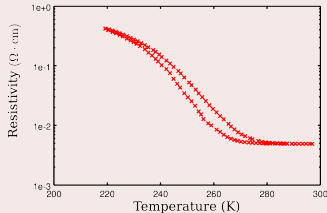
Samples supplied by M. Nakano, RKIEN



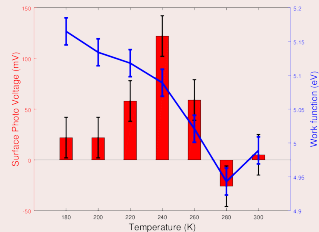
Curious behaviour in the range 120 K to 160 K, far below  $T_{MI}$   
Effect of substrate?

# Temperature Dependent SPV in W:VO<sub>2</sub>

## $\rho(T)$ and SPV(T)



Measurement by Nir Kedem



$\rho(T)$  magnitude and  $T_{MI}$ -range agrees with literature ([7],[10])  
 $\Delta\varphi_{MI}$  observed before; direction & magnitude unclear ([6],[8])  
 Gradual gap opening process → appearance of SPV  
 Sign of SPV identifies sample as n-type → W-doping

## Discussion & Conclusion

### We showed that...

- CPD is in excellent agreement with established systems
- SPV  $\sim 12\%$  too low. Shadowing?
- CPD(T) reproducible and interesting
- CPD(T) & SPV(T) reasonable
- Lakeshore + Mc Allister + LED is a viable experimental system for SPV(T)
- System has successfully been used in that configuration since 2014, publication forthcoming [11]



# List of References

## Literature and links

- [1] L. Kronik & Y. Shapira *Surf. Sci. Rep.*, **37(1-5)**, 1999
- [2] Besocke Website
- [3] Lakeshore Website
- [4] LEDengin Website
- [5] D. Cahen *et al. Appl. Phys. Lett.*, **101**, 2012
- [6] K. Shibuya *et al. Phys Rev. B*, **82(20)**, 2010
- [7] C. Ko *et al. ACS Appl. Mater. Interfaces*, **3(9)**, 2011
- [8] H. Yin *et al. ACS Appl. Mater. Interfaces*, **3(6)**, 2011
- [9] M. Nakano *et al. Nature*, **487(7408)**, 2012
- [10] K. Shibuya *et al. Appl. Phys. Lett.*, **96**, 2010
- [11] D. Cahen *et al. J. Phys. Chem. Lett.*, forthcoming

## Some more background. . .

### ...about my M.Sc. project

- Research carried out in 13/14 at  
The Weizmann Institute of  
Science
- Project had two parts: P(VDF)  
& SPV(T)
- Only part two was presented



# Acknowledgements

## Thanks! to...

Prof. David Cahen	for his supervision
Dr. Hugo Meekes	for his spontaneous support
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